

Ordering Information

Part Number	Marking	Package	Packing Method
FJP5555TU	J5555	TO-220	Rail

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter	Value	Units
BV _{CBO}	Collector-Base Voltage	1050	V
BV _{CEO}	Collector-Emitter Voltage	400	V
BV _{EBO}	Emitter-Base Voltage	14	V
۱ _C	Collector Current (DC)	5	A
I _{CP}	Collector Current (Pulse)	10	A
I _B	Base Current (DC)	2	Α
I _{BP}	Base Current (Pulse)	4	A
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 to +150	°C

Thermal Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter		Value	Units
P _D	Total Device Dissipation	$T_A = 25^{\circ}C$	1.38	W
		$T_{\rm C} = 25^{\circ}{\rm C}$	75	W
$R_{\theta ja}^{(1)}$	Thermal Resistance, Junction to Ambient		90	°C/W
$R_{\theta jc}^{(2)}$	Thermal Resistance, Junction to Case		1.66	°C/W

Notes:

1. $R_{\theta ja}$ test board and fixture under natural convection, JESD51-10 recommended thermal test board.

2. $R_{\theta ic}$ test fixture under infinite cooling condition.

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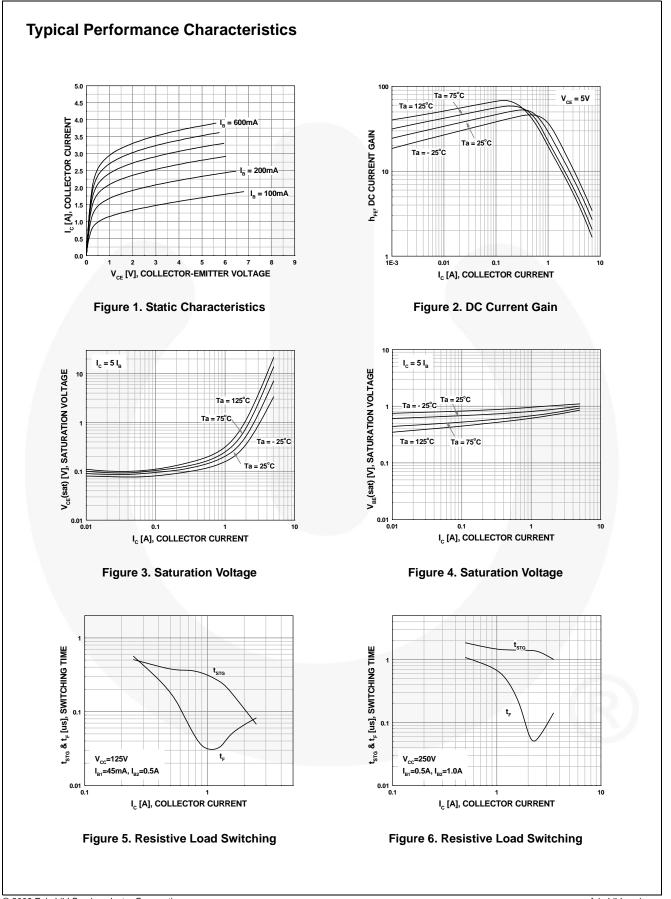
Electrical Characteristics⁽³⁾

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

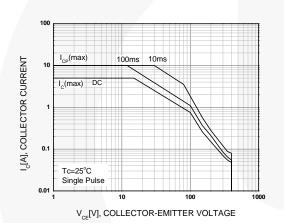
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Voltage	$I_{C} = 500 \ \mu A, \ I_{E} = 0$	1050			V
BV _{CEO}	Collector-Emitter Voltage	$I_{C} = 5 \text{ mA}, I_{B} = 0$	400			V
BV_{EBO}	Emitter-Base Voltage	$I_{\rm E} = 500 \ \mu {\rm A}, \ I_{\rm C} = 0$	14			V
h _{FE}	DC Current Gain	$V_{CE} = 5 V, I_{C} = 10 mA$	10			
	De current Gain	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 0.8 \text{ A}$	20		40	
	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 0.2 A			0.5	V
V _{CE} (sat)		I _C = 3.5 A, I _B = 1.0 A			1.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 3.5 A, I _B = 1.0 A			1.2	V
C _{ob}	Output Capacitance	V _{CB} = 10 V, f = 1 MHz		45		pF
t _{ON}	Turn-On Time	V _{CC} = 125 V, I _C = 0.5 A,			1.0	μs
t _{STG}	Storage Time	$ _{B_1} = 45 \text{ mA}, _{B_2} = 0.5 \text{ A}, _{R_1} = 250 \Omega$			1.2	μs
t _F	Fall Time				0.3	μs
t _{ON}	Turn-On Time	$V_{CC} = 250 \text{ V}, \text{ I}_{C} = 2.5 \text{ A}, \\I_{B1} = 0.5 \text{ A}, \text{ I}_{B2} = 1.0 \text{ A}, \\R_{L} = 100 \Omega$			2.0	μs
t _{STG}	Storage Time				2.5	μs
t _F	Fall Time				0.3	μs
EAS	Avalanche Energy	L = 2 mH	6			mJ

Note:

3. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2%.



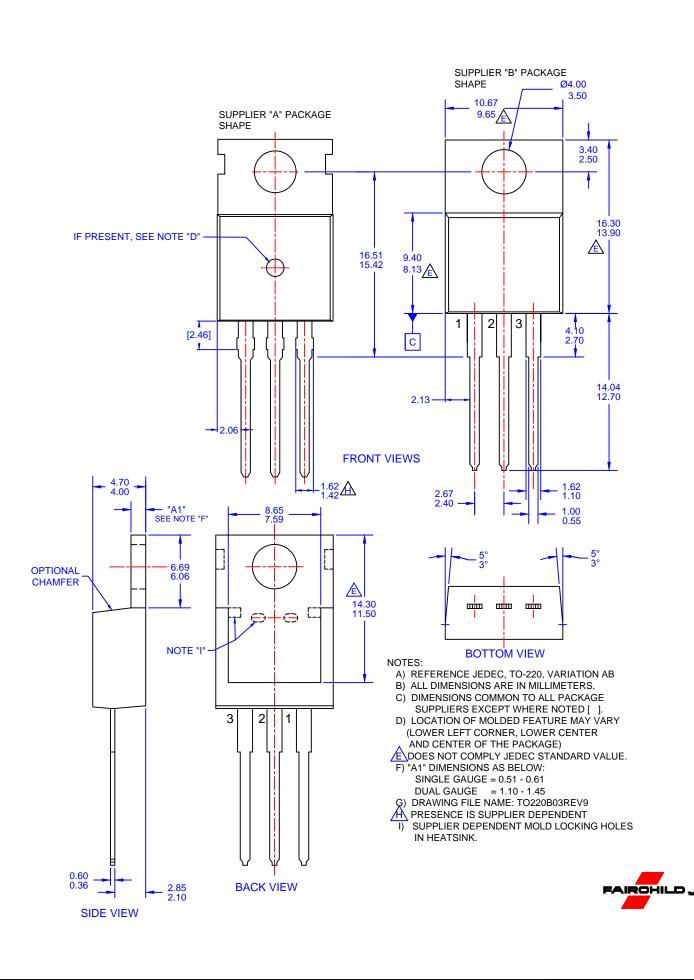
Typical Performance Characteristics (Continued) 100 90 80 I_c [A], COLLECTOR CURRENT P_c[W], POWER DISSIPATION 70 60 50 40 30 20 V_{cc}=50V, L=1mH 10 I_{B1}=3A, R_{B2}=0 0 L 0 1 L 10 25 75 100 1000 V_{CE} [V], COLLECTOR-EMITTER VOLTAGE 50 100 125 150 175 1000 Tc[°C], CASE TEMPERATURE Figure 7. Reverse Biased Safe Operating Area Figure 8. Power Derating





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